XP161A11A1PR

TOREX

Power MOS FET

- ◆N-Channel Power MOS FET
- ◆DMOS Structure
- ◆Low On-State Resistance: 0.105Ω (max)
- ◆Gate Protect Diode Built-in
- ◆Ultra High-Speed Switching
- ◆SOT-89 Package

■Applications

- ●Notebook PCs
- ●Cellular and portable phones
- ●On-board power supplies
- ●Li-ion battery systems

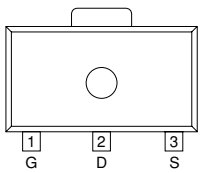
■General Description

The XP161A11A1PR is an N-Channel Power MOS FET with low on-state resistance and ultra high-speed switching characteristics.
Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.
A gate protect diode is built-in to prevent static damage.
The small SOT-89 package makes high density mounting possible.

■Features

Low on-state resistance : Rds(on)=0.065Ω(Vgs=10V)
: Rds(on)=0.105Ω(Vgs=4.5V)
Ultra high-speed switching
Gate Protect Diode Built-in
Operational Voltage : 4.5V
High density mounting : SOT-89

■Pin Configuration



SOT-89
(TOP VIEW)

■Pin Assignment

PIN NUMBER	PIN NAME	FUNCTION
1	G	Gate
2	D	Drain
3	S	Source

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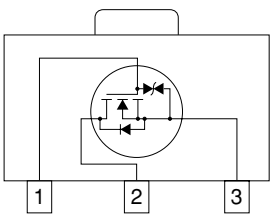
■Equivalent Circuit



N-Channel MOS FET
(1 device built-in)

■Absolute Maximum Ratings

Ta=25˚C

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	Vdss	30	V
Gate-Source Voltage	Vgss	±20	V
Drain Current (DC)	Id	4	A
Drain Current (Pulse)	Idp	16	A
Reverse Drain Current	Idr	4	A
Continuous Channel Power Dissipation (note)	Pd	2	W
Channel Temperature	Tch	150	˚C
Storage Temperature	Tstg	-55~150	˚C

Note: When implemented on a ceramic PCB

■Electrical Characteristics

DC Characteristics

Ta=25℃

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Drain Cut-off Current	Idss	Vds=30V, Vgs=0V			10	μA
Gate-Source Leakage Current	Igss	Vgs=±20V, Vds=0V			±10	μA
Gate-Source Cut-off Voltage	Vgs(off)	Id=1mA, Vds=10V	1.0		2.5	V
Drain-Source On-state Resistance (note)	Rds(on)	Id=2A, Vgs=10V		0.05	0.065	Ω
		Id=2A, Vgs=4.5V		0.075	0.105	Ω
Forward Transfer Admittance (note)	|Yfs|	Id=2A, Vds=10V		5.5		S
Body Drain Diode Forward Voltage	Vf	If=4A, Vgs=0V		0.85	1.1	V

Note: Effective during pulse test.

Dynamic Characteristics

Ta=25℃

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Capacitance	Ciss	Vds=10V, Vgs=0V f=1MHz		270		pF
Output Capacitance	Coss			150		pF
Feedback Capacitance	Crss			55		pF

Switching Characteristics

Ta=25℃

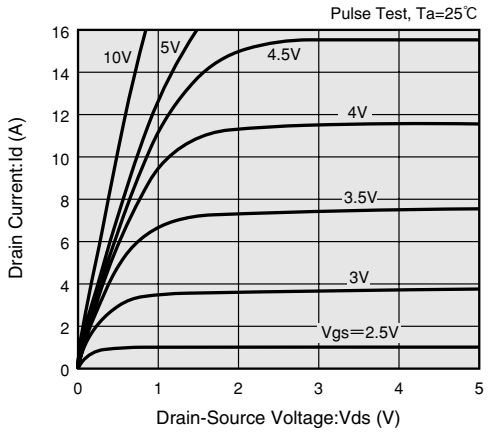
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Turn-on Delay Time	td (on)	Vgs=5V, Id=2A Vdd=10V		10		ns
Rise Time	tr			15		ns
Turn-off Delay Time	td (off)			35		ns
Fall Time	tf			15		ns

Thermal Characteristics

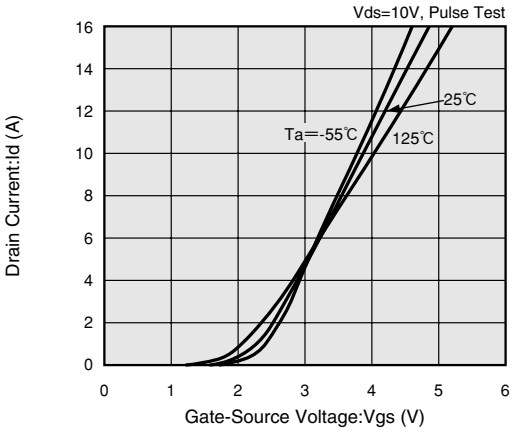
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Thermal Resistance (channel-ambience)	Rth (ch-a)	Implement on a ceramic PCB		62.5		℃/W

■Typical Performance Characteristics

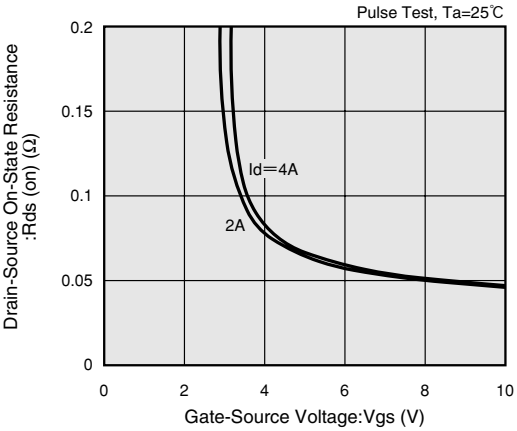
DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE



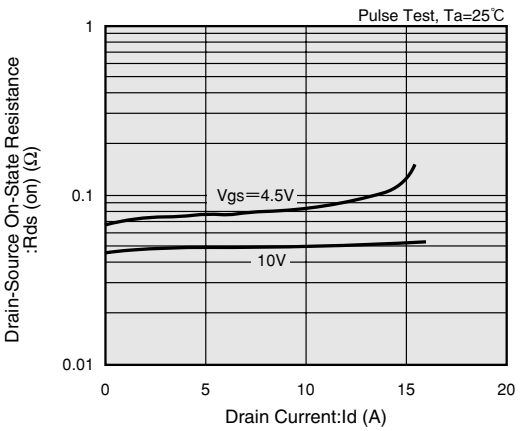
DRAIN CURRENT vs. GATE-SOURCE VOLTAGE



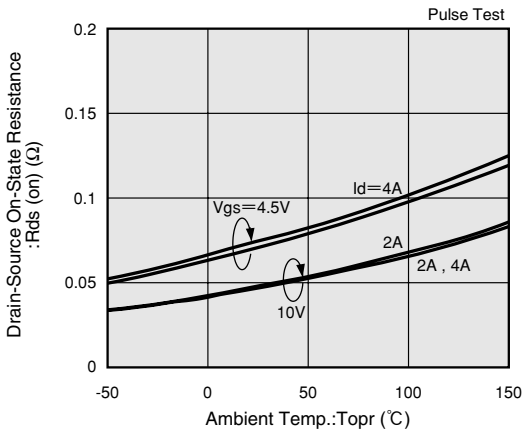
DRAIN-SOURCE ON-STATE RESISTANCE
vs. GATE-SOURCE VOLTAGE



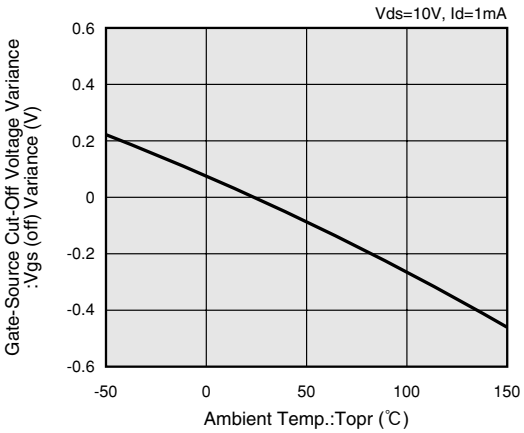
DRAIN-SOURCE ON-STATE RESISTANCE
vs. DRAIN CURRENT



DRAIN-SOURCE ON-STATE RESISTANCE
vs. AMBIENT TEMPERATURE



GATE-SOURCE CUT-OFF VOLTAGE VARIANCE
vs. AMBIENT TEMPERATURE



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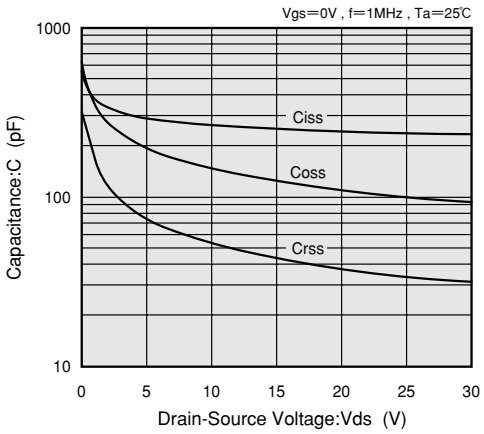
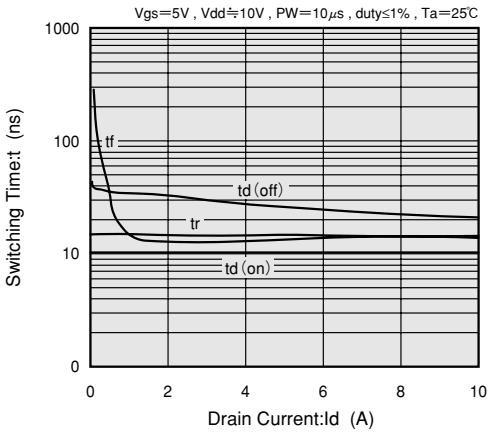
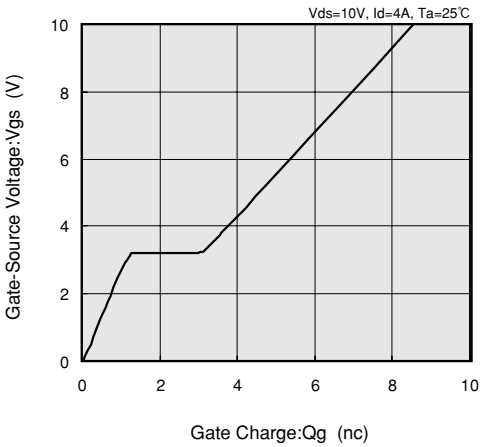
CAPACITANCE vs. DRAIN-SOURCE VOLTAGE



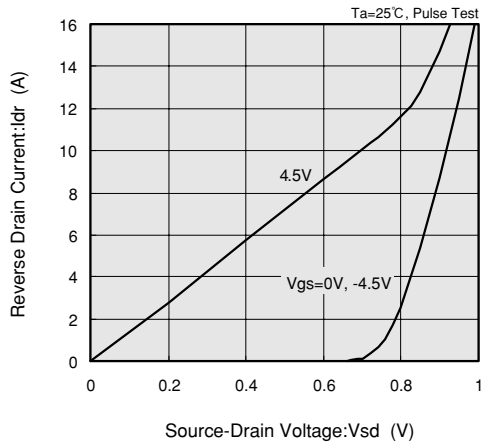
SWITCHING TIME vs. DRAIN CURRENT



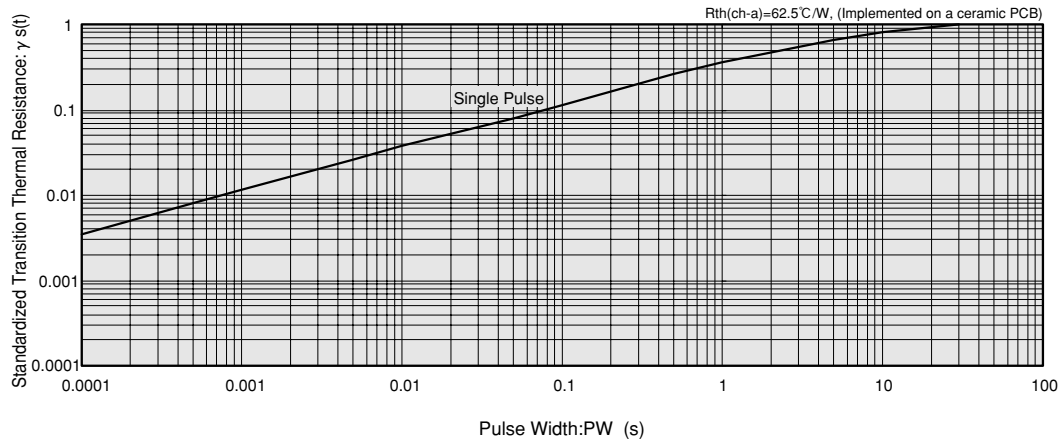
GATE-SOURCE VOLTAGE vs. GATE CHARGE



REVERSE DRAIN CURRENT
vs. SOURCE-DRAIN VOLTAGE



STANDARDIZED TRANSITION THERMAL RESISTANCE vs. PULSE WIDTH



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